# **Quad 2-Input XOR Gate**

The MC74VHC86 is an advanced high speed CMOS 2-input Exclusive-OR gate fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7 V, allowing the interface of 5 V systems to 3 V systems.

#### **Features**

- High Speed:  $t_{PD} = 4.8 \text{ ns}$  (Typ) at  $V_{CC} = 5 \text{ V}$
- Low Power Dissipation:  $I_{CC} = 2 \mu A \text{ (Max)}$  at  $T_A = 25 \text{°C}$
- High Noise Immunity:  $V_{NIH} = V_{NIL} = 28\% V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2 V to 5.5 V Operating Range
- Low Noise: V<sub>OLP</sub> = 0.8 V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: Human Body Model (HBM) > 2000 V;
   Machine Model > 200 V
- Chip Complexity: 56 FETs or 14 Equivalent Gates
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

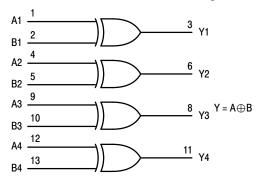


Figure 1. Logic Diagram

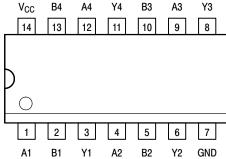


Figure 2. Pinout: 14-Lead Packages (Top View)



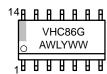
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MARKING DIAGRAMS



SOIC-14 D SUFFIX CASE 751A

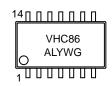




TSSOP-14 DT SUFFIX CASE 948G







A = Assembly Location

WL, L = Wafer Lot Y, YY = Year

WW, W = Work Week

G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

#### **FUNCTION TABLE**

In	Output	
Α	В	Y
L	L	L
L	Н	H
Н	L	H
Н	Н	L

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

#### **MAXIMUM RATINGS**

Symbol	Parameter	r	Value	Unit
V <sub>CC</sub>	DC Supply Voltage		-0.5 to +7.0	V
V <sub>in</sub>	DC Input Voltage		-0.5 to +7.0	V
V <sub>out</sub>	DC Output Voltage	-0.5 to V <sub>CC</sub> +0.5	V	
I <sub>IK</sub>	Input Diode Current	-20	mA	
I <sub>OK</sub>	Output Diode Current		±20	mA
I <sub>out</sub>	DC Output Current, per Pin		±25	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GI	ND Pins	±50	mA
P <sub>D</sub>	Power Dissipation in Still Air,	SOIC Packages <sup>†</sup> TSSOP Package <sup>†</sup>	500 450	mW
T <sub>stg</sub>	Storage Temperature		-65 to +150	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range GND  $\leq$  ( $V_{in}$  or  $V_{out}$ )  $\leq$   $V_{CC}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

†Derating SOIC Packages: - 7 mW/°C from 65° to 125°C

TSSOP Package: - 6.1 mW/°C from 65° to 125°C

#### RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage		2.0	5.5	V
V <sub>in</sub>	DC Input Voltage		0	5.5	V
V <sub>out</sub>	DC Output Voltage		0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature, All Package Types		-55	+125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$ $V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	0	100 20	ns/V

# DC ELECTRICAL CHARACTERISTICS

			V <sub>CC</sub>		T <sub>A</sub> = 25°C	;	T <sub>A</sub> = -55°C	to +125°C	
Symbol	Parameter	Test Conditions	v	Min	Тур	Max	Min	Max	Unit
V <sub>IH</sub>	High-Level Input Voltage		2.0 3.0 to 5.5	1.50 V <sub>CC</sub> x 0.7			1.50 V <sub>CC</sub> x 0.7		V
V <sub>IL</sub>	Low-Level Input Voltage		2.0 3.0 to 5.5			0.50 V <sub>CC</sub> x 0.3		0.50 V <sub>CC</sub> x 0.3	V
V <sub>OH</sub>	High-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \mu A$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		V
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -4 \text{ mA}$ $I_{OH} = -8 \text{ mA}$	3.0 4.5	2.58 3.94			2.48 3.80		
V <sub>OL</sub>	Low-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50  \mu\text{A}$	2.0 3.0 4.5		0 0 0	0.1 0.1 0.1		0.1 0.1 0.1	V
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 4 \text{ mA}$ $I_{OL} = 8 \text{ mA}$	3.0 4.5			0.36 0.36		0.44 0.44	
I <sub>in</sub>	Input Leakage Current	V <sub>in</sub> = 5.5 V or GND	0 to 5.5			±0.1		±1.0	μΑ
I <sub>CC</sub>	Quiescent Supply Current	$V_{in} = V_{CC}$ or GND	5.5			2.0		20.0	μΑ

# AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ns}$ )

				T <sub>A</sub> = 25°C		T <sub>A</sub> = -55°C to +125°C			
Symbol	Parameter	Test Condi	tions	Min	Тур	Max	Min	Max	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Propagation Delay, A or B to Y	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	$C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		7.0 9.5	11.0 14.5	1.0 1.0	13.0 16.5	ns
		$V_{CC} = 5.0 \pm 0.5 \text{ V}$	$C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		4.8 6.3	6.8 8.8	1.0 1.0	8.0 10.0	
C <sub>in</sub>	Input Capacitance				4	10		10	pF

		Typical @ 25°C, V <sub>CC</sub> = 5.0 V	
$C_{PD}$	Power Dissipation Capacitance (Note 1.)	18	pF

<sup>1.</sup> C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I<sub>CC(OPR)</sub> = C<sub>PD</sub> • V<sub>CC</sub> • f<sub>in</sub> + I<sub>CC</sub>/4 (per gate). C<sub>PD</sub> is used to determine the no–load dynamic power consumption; P<sub>D</sub> = C<sub>PD</sub> • V<sub>CC</sub><sup>2</sup> • f<sub>in</sub> + I<sub>CC</sub> • V<sub>CC</sub>.

# **NOISE CHARACTERISTICS** (Input $t_r = t_f = 3.0$ ns, $C_L = 50$ pF, $V_{CC} = 5.0$ V, Measured in SOIC Package)

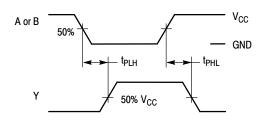
		T <sub>A</sub> =	25°C	
Symbol	Characteristic	Тур	Max	Unit
V <sub>OLP</sub>	Quiet Output Maximum Dynamic V <sub>OL</sub>	0.3	0.8	V
V <sub>OLV</sub>	Quiet Output Minimum Dynamic V <sub>OL</sub>	-0.3	-0.8	V
V <sub>IHD</sub>	Minimum High Level Dynamic Input Voltage		3.5	V
V <sub>ILD</sub>	Maximum Low Level Dynamic Input Voltage		1.5	V

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC74VHC86DR2G	SOIC-14 (Pb-Free)	2500 / Tape & Reel
MC74VHC86DTG	TSSOP-14 (Pb-Free)	96 Units / Rail
MC74VHC86DTR2G	TSSOP-14 (Pb-Free)	2500 / Tape & Reel
NLVVHC86ADTR2G*	TSSOP-14 (Pb-Free)	2500 / Tape & Reel
MC74VHC86MELG	SOEIAJ-14 (Pb-Free)	2000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging

Specifications Brochure, BRD8011/D.
\*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP Capable.



TEST POINT OUTPUT DEVICE **UNDER** TEST

\*Includes all probe and jig capacitance

Figure 3. Switching Waveforms

Figure 4. Test Circuit

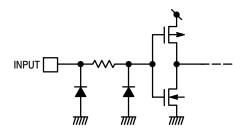
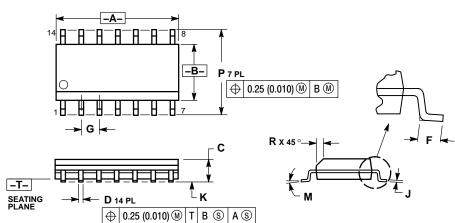


Figure 5. Input Equivalent Circuit

#### **PACKAGE DIMENSIONS**

#### SOIC-14 CASE 751A-03 **ISSUE J**



#### NOTES:

- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: MILLIMETER.

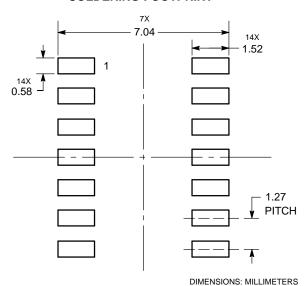
  3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.

  4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

  5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	8.55	8.75	0.337	0.344
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
М	0 °	7°	0 °	7 °
Р	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

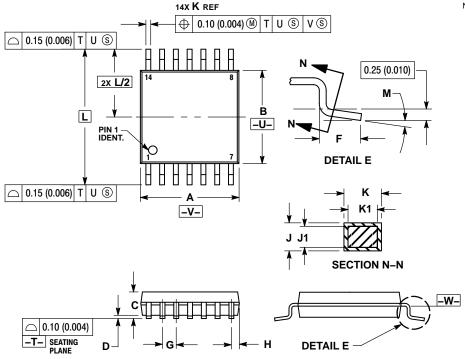
# **SOLDERING FOOTPRINT\***



<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### PACKAGE DIMENSIONS

#### TSSOP-14 **DT SUFFIX** CASE 948G **ISSUE B**



#### NOTES:

- DTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: MILLIMETER.

  3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

  4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

  5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

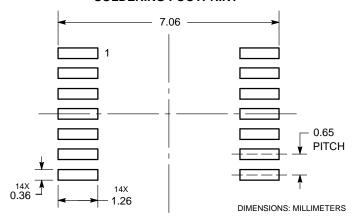
  6. TERMINAL NUMBERS ARE SHOWN FOR
- CONDITION.

  6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

  7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

	MILLIN	IETERS	S INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
C	-	1.20	-	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	BSC	0.026 BSC	
Н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
Κ	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
٦	6.40 BSC		0.252 BSC	
М	0 °	8 °	0°	8 °

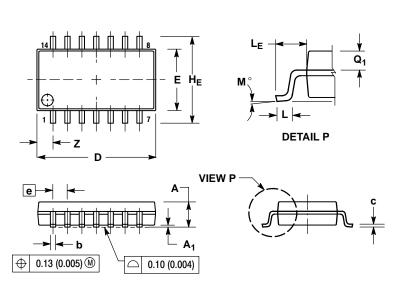
#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### PACKAGE DIMENSIONS

#### SOEIAJ-14 CASE 965 ISSUE B



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
  Y14.5M, 1982.
   CONTROLLING DIMENSION: MILLIMETER.
- CONTROLLING DIMENSION: MILLIMETER.
   DIMENSIONS D AND E DO NOT INCLUDE
   MOLD FLASH OR PROTRUSIONS AND ARE
   MEASURED AT THE PARTING LINE. MOLD FLASH
- OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
  4. TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.

  5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		MILLIMETERS INCH		HES
DIM	MIN	MAX	MIN	MAX	
Α		2.05		0.081	
A <sub>1</sub>	0.05	0.20	0.002	0.008	
b	0.35	0.50	0.014	0.020	
C	0.10	0.20	0.004	0.008	
D	9.90	10.50	0.390	0.413	
Е	5.10	5.45	0.201	0.215	
е	1.27 BSC		0.050	BSC	
HE	7.40	8.20	0.291	0.323	
L	0.50	0.85	0.020	0.033	
LE	1.10	1.50	0.043	0.059	
M	0 °	10°	0 °	10 °	
$Q_1$	0.70	0.90	0.028	0.035	
Z		1.42		0.056	

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